BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

General Purpose Transistors

NPN Silicon

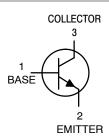
Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

www.onsemi.com



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	45	V
Collector - Base Voltage	V_{CBO}	50	V
Emitter - Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



6x = Device Codex = A, B, or C

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		I		1	
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _(BR) CEO	45	_	_	V
Collector – Emitter Breakdown Voltage $(V_{EB}=0,I_C=10\mu\text{A})$	V _{(BR)CES}	50	_	-	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	V _{(BR)EBO}	5.0	_	-	V
Collector Cutoff Current (V _{CB} = 20 V) (V _{CB} = 20 V, T _A = 150°C)	I _{CBO}	- -	_ _	100 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ (I_C = 100 \text{ mA}, \text{ V}_{CE} = 1.0 \text{ V}) \\ \text{BC817-16, SBC817-16} \\ \text{BC817-25, SBC817-25} \\ \text{BC817-40, SBC817-40} \\ \text{(I}_C = 500 \text{ mA, V}_{CE} = 1.0 \text{ V}) $	h _{FE}	100 160 250 40	- - -	250 400 600 –	ı
Collector – Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}		_	0.7	V
Base – Emitter On Voltage (I _C = 500 mA, V _{CE} = 1.0 V)	V _{BE(on)}	_	_	1.2	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	_	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	10	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]	
BC817-16LT1G			0000 (Table 9 Paul	
NSVBC817-16LT1G		SOT-23	3000 / Tape & Reel	
BC817-16LT3G	6A	(Pb-Free)	10.000 / Table 9. Paul	
SBC817-16LT3G			10,000 / Tape & Reel	
BC817-25LT1G			3000 / Tape & Reel	
SBC817-25LT1G	20	SOT-23		
BC817-25LT3G	6B	(Pb-Free)	40.000 (Tree 0 Deel	
SBC817-25LT3G			10,000 / Tape & Reel	
BC817-40LT1G		SOT-23	3000 / Tape & Reel	
SBC817-40LT1G				
BC817-40LT3G	6C	(Pb-Free)	40.000 /Taba 0 Bash	
SBC817-40LT3G			10,000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L

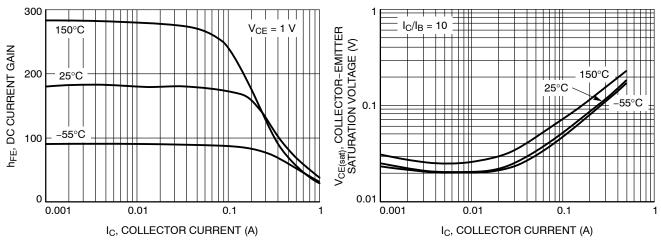


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

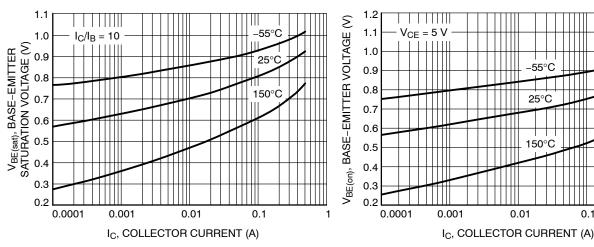
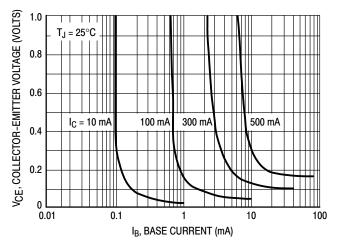


Figure 3. Base Emitter Saturation Voltage vs. **Collector Current**

Figure 4. Base Emitter Voltage vs. Collector Current

0.1

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L



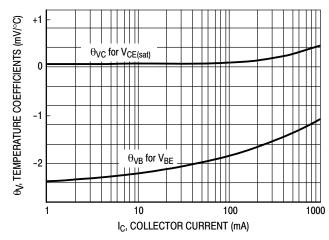


Figure 5. Saturation Region

Figure 6. Temperature Coefficients

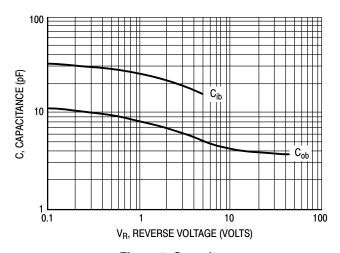


Figure 7. Capacitances

TYPICAL CHARACTERISTICS - BC817-25L, SBC817-25L

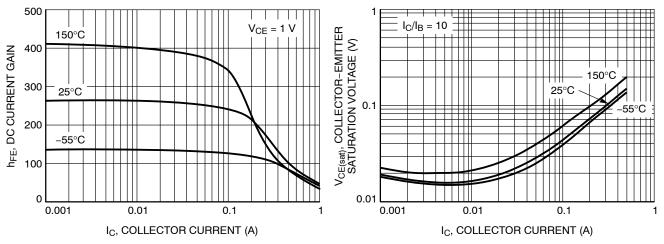


Figure 8. DC Current Gain vs. Collector Current

Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

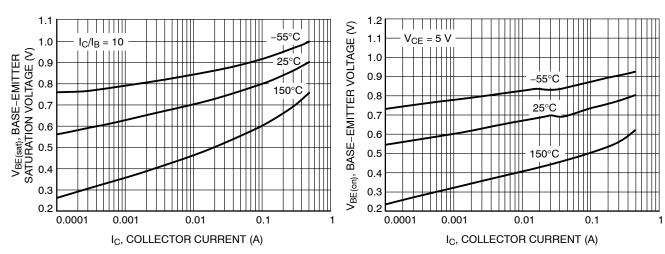


Figure 10. Base Emitter Saturation Voltage vs. Collector Current

Figure 11. Base Emitter Voltage vs. Collector Current

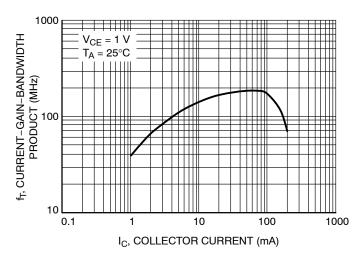
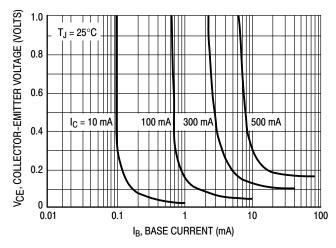


Figure 12. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-25L, SBC81725L



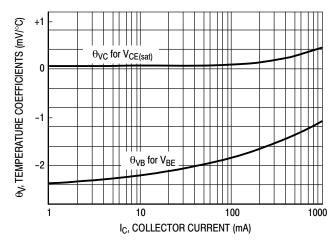


Figure 13. Saturation Region

Figure 14. Temperature Coefficients

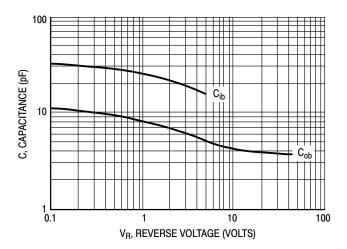


Figure 15. Capacitances

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L

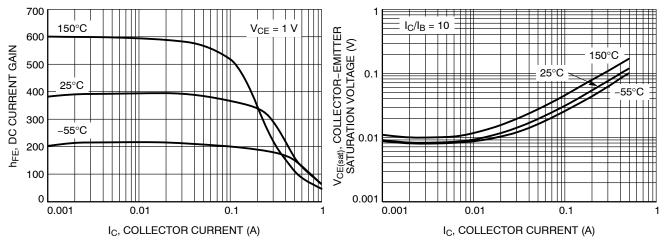


Figure 16. DC Current Gain vs. Collector Current

Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

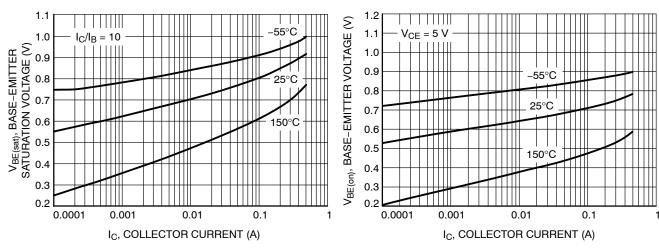


Figure 18. Base Emitter Saturation Voltage vs.
Collector Current

Figure 19. Base Emitter Voltage vs. Collector Current

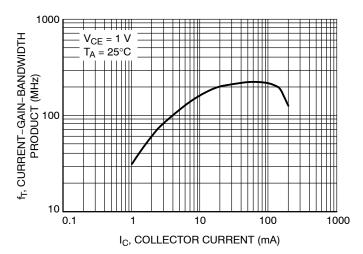
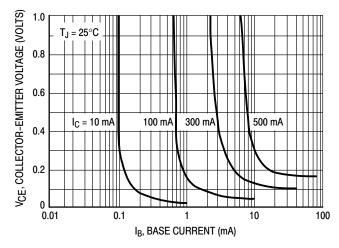


Figure 20. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L



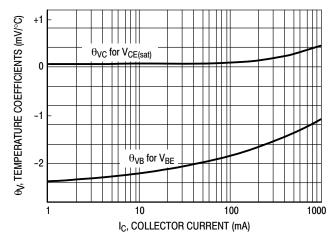


Figure 21. Saturation Region

Figure 22. Temperature Coefficients

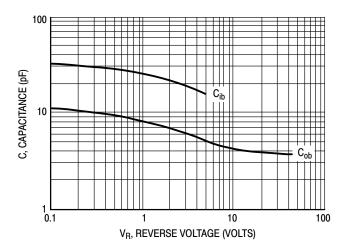


Figure 23. Capacitances

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

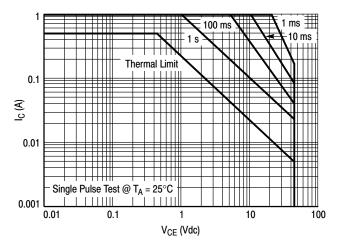


Figure 24. Safe Operating Area



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

0.017

0.021

0.094

0.022

0.027

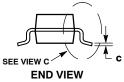
0.104

10°

SCALE 4:1 D Ε – 3X h **TOP VIEW**







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

PIN 1. RETURN

3. INPUT

3. ANODE

STYLE 28: PIN 1. ANODE 2. ANODE

2. OUTPUT

NOTES:

0.43

0.54

2.40

0.30

0.35

2.10

0°

ΗE

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
9	1 78	1 90	2 04	0.070	0.075	0.080

0.55

0.69

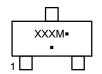
2.64

10° 0° **GENERIC MARKING DIAGRAM***

0.012

0.014

0.083



XXX = Specific Device Code

= Date Code

PIN 1. ANODE 2. CATHODE

3. GATE

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	N	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:

PIN 1. ANODE

ANODE

CATHODE

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1

PIN 1. GATE 2. DRAIN

3. SOURCE

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

PIN 1. GATE

2. SOURCE

3. CATHODE

DRAIN

STYLE 27: PIN 1. CATHODE 2. CATHODE

PIN 1. CATHODE 2. ANODE

3. NO CONNECTION

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative